

BDW93CFP BDW94CFP

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- MONOLITHIC DARLINGTON CONFIGURATION
- COMPLEMENTARY PNP NPN DEVICES
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE
- FULLY MOLDED INSULATED PACKAGE
- 2000 V DC INSULATION (U.L. COMPLIANT)

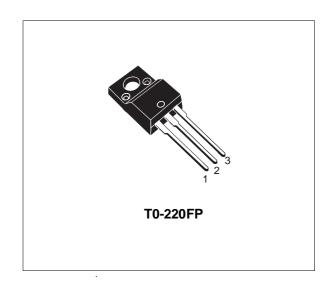
APPLICATIONS

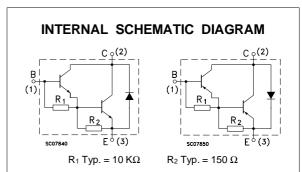
 LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The BDW93CFP is a silicon Epitaxial-Base NPN transistor in monolithic Darlington configuration mounted in TO-220FP fully molded insulated package. It is intented for use in power linear and switching applications.

The complementary PNP type is the BDW94CFP.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit	
		NPN	BDW93CFP		
		PNP	BDW94CFP		
V _{CBO}	Collector-Base Voltage (I _E = 0)		100	V	
Vceo	Collector-Emitter Voltage (I _B = 0)		100	V	
Ic	Collector Current		12	А	
I _{CM}	Collector Peak Current		15	А	
I _B	Base Current		0.2	Α	
P _{tot}	Total Dissipation at T _c ≤ 25 °C		33	W	
T _{stg}	Storage Temperature		-65 to 150	°C	
Tj	Max. Operating Junction Temperature		150	°C	

For PNP types voltage and current values are negative.

September 2001 1/4

BDW93CFP / BDW94CFP

THERMAL DATA

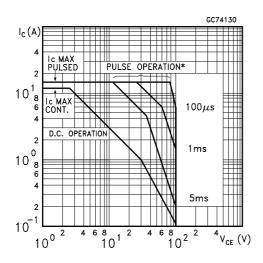
ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Co	Min.	Тур.	Max.	Unit	
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 100 V V _{CB} = 100 V	T _{case} = 150 °C			100 5	μA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 80 V				1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				2	mA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA		100			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	I _C = 5 A I _C = 10 A	$I_B = 20 \text{ mA}$ $I_B = 100 \text{ mA}$			2 3	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 5 A I _C = 10 A	I _B = 20 mA I _B = 100 mA			2.5 4	V V
h _{FE} *	DC Current Gain	I _C = 3 A I _C = 5 A I _C = 10 A	$V_{CE} = 3 V$ $V_{CE} = 3 V$ $V_{CE} = 3 V$	1000 750 100		20000	
V _F *	Parallel-diode Forward Voltage	I _F = 5 A I _F = 10 A			1.3 1.8	2 4	V V
h _{fe}	Small Signal Current Gain	I _C = 1 A f = 1 MHz	V _{CE} = 10 V	20			

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

For PNP types voltage and current values are negative.

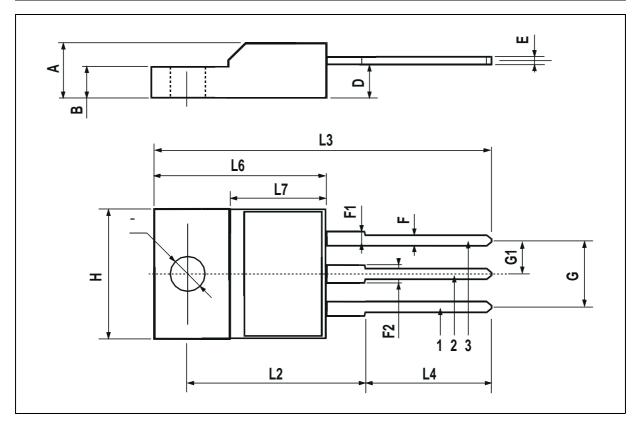
Safe Operating Area



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TO-220FP MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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